

Listing of Claims:

1. (Currently Amended) [[A]] An optoelectronic semiconductor component having a thin-film semiconductor body (2) arranged on a carrier (4) of the optoelectronic semiconductor component, wherein the carrier (4) contains germanium.

2. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 1, wherein the thin-film semiconductor body (2) is soldered onto the carrier (4).

3. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 1, wherein the thin-film semiconductor body (2) is soldered onto the carrier (4) by means of a gold-containing solder.

4. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 1, wherein the thin-film semiconductor body (2) comprises a plurality of individual layers.

5. (Currently Amended) The optoelectronic semiconductor component as claimed in claim [[1]] 4, wherein the thin-film semiconductor body (2) or at least one of ~~the~~ said plural individual layers contains a type III-V compound semiconductor.

6. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 5, wherein the thin-film semiconductor body (2) or at least one of ~~the~~ said plural individual layers contains $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{P}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

7. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 5, wherein the thin-film semiconductor (2) or at least one of ~~the~~ said plural individual layers contains $\text{In}_x\text{As}_y\text{Ga}_{1-x-y}\text{P}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

8. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 5, wherein the thin-film semiconductor body (2) or at least one of said plural individual layers contains $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{As}$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$ or $\text{In}_x\text{Ga}_{1-x}\text{As}_{1-y}\text{N}_y$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$.

9. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 5, wherein the thin-film semiconductor body (2) or at least one of said plural individual layers contains a nitride compound semiconductor. ~~[[,]] in particular $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$ [[.]]~~

10. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 1, wherein the thin-film semiconductor body (2) has a radiation-emitting active region.

11. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 1, wherein a mirror layer[[,]] ~~preferably a metallic mirror layer~~[[,]] is arranged between the thin-film semiconductor body (2) and the carrier (4).

12. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 11, wherein a dielectric layer is at least partially arranged between the thin-film semiconductor body (2) and the mirror layer.

13. (Currently Amended) A method for producing [[a]] an optoelectronic semiconductor component having a thin-film conductor body (2) arranged on a carrier (4), ~~having~~ comprising the steps of:

- a) growing the thin-film semiconductor body on a substrate[[,]];
- b) applying the carrier (4) to a side of the thin-film semiconductor body (2) that is remote from the substrate (1)[[,]]; and
- c) stripping the thin-film semiconductor body (2) from the substrate[[,]]; wherein the carrier (4) contains germanium.

14. (Currently Amended) The method as claimed in claim 13, wherein the substrate is eroded away in step c)[[,]] ~~in particular ground away and/or etched away, in step c)~~[[.]]

15. (Currently Amended) The method as claimed in claim 13, wherein the semiconductor body is stripped from the substrate (1) by laser irradiation in step c).

16. (Previously Presented) The method as claimed in claim 13, wherein the carrier is soldered on in step b).

17. (Currently Amended) The method as claimed in claim 13, wherein a gold layer (~~3, 3a, 3b~~) is arranged on at least one of that side of the thin-film semiconductor body (~~2~~) which faces the carrier ~~and/or~~ and on that side of the carrier which faces the thin-film semiconductor body (~~2~~), and wherein said gold layer, when the carrier is soldered on in step b), at least partially forms a melt containing gold and germanium.

18. (Currently Amended) The method as claimed in claim 13, wherein prior to step b), a layer containing gold and germanium is applied on at least one of that side of the thin-film semiconductor body (~~2~~) which faces the carrier ~~and/or~~ and on that side of the carrier which faces the thin-film semiconductor body (~~2~~).

19. (Currently Amended) The method as claimed in claim 13, for producing [[a]] an optoelectronic semiconductor component having a thin-film body arranged on a carrier that contains germanium.

20. (Previously Presented) The semiconductor component as claimed in claim 1, wherein the semiconductor component is a luminescence diode.

21. (Currently Amended) The optoelectronic semiconductor component as claimed in claim 20, wherein the semiconductor component is a light emitting diode or a laser diode.

22. (Currently Amended) The method as claimed in claim 13, wherein the optoelectronic semiconductor component is a luminescence diode.

23. (Currently Amended) The method as claimed in claim 22, wherein the optoelectronic semiconductor component is a light-emitting diode or a laser diode.

24. (New) The optoelectronic semiconductor component as claimed in claim 9, wherein the thin-filmed semiconductor body or at least one of the individual layers contains a nitride compound semiconductor in accordance with the relationship $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$.

25. (New) The optoelectronic semiconductor component as claimed in claim 11, wherein the mirror layer comprises a metallic mirror layer.

26. (New) The method as claimed in claim 14, wherein the substrate is eroded away in step c) by at least one of grinding and etching.

27. (New) The optoelectronic semiconductor component as claimed in claim 1, wherein the thin-film semiconductor body is a thin-film luminescence diode chip.

28. (New) The method as claimed in claim 13, wherein the thin-film semiconductor body is a thin-film luminescence diode chip.